Crystal Structure and Physical Properties of (BMDT-TTF)SbF6

Reizo KATO, Hayao KOBAYASHI,* and Akiko KOBAYASHI[†]
Department of Chemistry, Faculty of Science, Toho University,
Funabashi, Chiba 274

+Department of Chemistry, Faculty of Science, The University of Tokyo, Hongo, Bunkyo-ku, Tokyo 113

In a crystal of (BMDT-TTF)SbF $_6$, quasi two-dimensional(2D) intermolecular interactions of BMDT-TTF molecules are observed. This compound was a semiconductor with fairly high room temperature conductivity (ca. 1 S cm $^{-1}$), and would be a simple model compound for the consideration of electron-electron interaction in quasi 2D half-filled band system.

In the molecular conductor, the 1:1 salt comprised of one electron (hole) for every molecule has been considered low conductive. For example, Rb•TCNQ-II with a one-dimensional uniform TCNQ column is not metallic, in contrast to TTF•TCNQ and NMP•TCNQ containing similar TCNQ column. 1) This indicates that a simple band picture with a half-filled conduction band should be affected by the electron-electron interaction. It is well-known that there exists antiferromagnetic interaction between adjacent sites in the highly correlated band system. Three-dimensional magnetic orderness, however, does not develop usually in the organic conductors because of its strong one-dimensionality. Recent progress of the molecular conductor has provided the multi-dimensional system. 2) We are much interested in the possibily of the magnetic orderness in the multi-dimensional system with the half-filled band. In this paper, we report crystal structure of (BMDT-TTF)SbF₆ (BMDT-TTF; bis(methylenedithio)tetrathiafulvalene) and indicate that this compound has very simple half-filled band with weak one-dimensionality (quasi two-dimensional character).

Black elongated plates of (BMDT-TTF)SbF₆ were obtained by the electrochemical oxidation of a 1,1,2-trichloroethane solution containing BMDT-TTF and (n-C₄H₉)₄N SbF₆ at a constant current of 1 μ A. Crystal data: C₈H₄S₈SbF₆, triclinic, space group PT, a=9.573(3), b=7.500(2), c=5.633(2) Å, α =100.20(3), β =91.61(3), γ =90.96 (2)°, V=397.7 Å³, Z=1. Intensities were measured on a Rigaku automated four-circle diffractometer with Mo K α radiation up to 2 θ =60°. Independent 2892 reflections (|F₀|>3 σ (|F₀|)) were used for calculations. The structure was solved by the direct method and refined to the conventional R value of 0.039. The final atomic coordinates are given in Table 1.

The crystal structure of (BMDT-TTF)SbF $_6$ is shown in Fig. 1. The BMDT-TTF

Table 1. Fractional atomic coordinates (\times 10 3 for H atoms; \times 10 4 for others) with their

estimated standard deviations					
Atom	x	У	z		
Sb	0	0	0		
F(1)	1854(3)	-567(5)	764(7)		
F(2)	634(4)	2261(4)	-656(7)		
F(3)	247(5)	-1115(5)	-3235(7)		
S(1)	3276(1)	1581(1)	6583(2)		
S(2)	5009(1)	1869(1)	2457(2)		
S(3)	1816(1)	5090(2)	6023(2)		
S(4)	3524(1)	5331(2)	1771(2)		
C(1)	4637(4)	733(5)	4794(8)		
C(2)	2983(4)	3381(6)	5131(8)		
C(3)	3782(5)	3509(5)	3229(8)		
C(4)	1844(6)	5828(7)	3123(10)		
H(1)	78(8)	501(10)	207(15)		
H(2)	173(9)	745(10)	357(17)		

Table 2. Comparison of bond lengths (\mathring{A}) of BMDT-TTF(neutral) and BMDT-TTF+ The bond lengths b, c, and d are average values, with an approximated D2h symmetry.

	neutral	BMDT-TTF+
a	1.327	1.361
b	1.766	1.730
С	1.738	1.722
d	1.334	1.350

Table 3. Overlap integrals $S_{\mathbf{v}}$ (× 10³) of the HOMO in (BMDT-TTF)SbF₆

Sb	-5.10	
$s_{f c}$	-12.48	
S _{b+c}	0	
s_{b-c}	0.81	
S-a+b	0.23	

 $\mathbf{S}_{\mathbf{v}}$ indicates the overlap integral between molecules interrelated by the translation vector $\mathbf{v}_{\:\raisebox{1pt}{\text{\circle*{1.5}}}}$

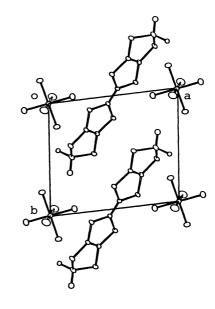


Fig. 1. Crystal structure of $(BMDT-TTF)SbF_6$.

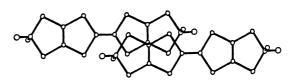


Fig. 2. Mode of intermolecular overlapping.

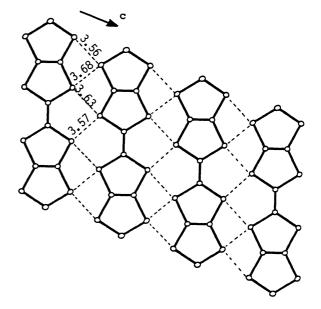
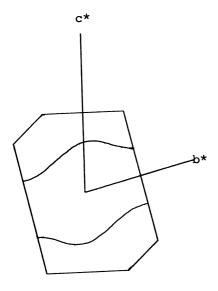


Fig. 3. Side-by-side arrangement of BMDT-TTF molecules.



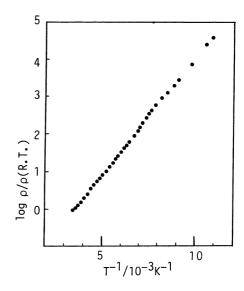


Fig. 4. "Artificial" Fermi surface of (BMDT-TTF)SbF₆ obtained by a simple tight-binding approximation.

Fig. 5. Electrical resistivity of (BMDT-TTF)SbF₆ along the c axis.

molecule lies on an inversion center, and almost planar. Lengthened C=C distances (a, d; in Table 2) and shortened C-S distances (b, c) of BMDT-TTF+ compared with those of neutral BMDT-TTF³⁾ are in good agreement with the result of the molecular orbital calculation; the HOMO (highest occupied molecular orbital) has nodal planes on every C-S bond. This is just the same as we can see in the BEDT-TTF compound. 4) The BMDT-TTF units are repeated along the b axis in a face-to-face manner. In this direction, an adjacent molecule is largely shifted along the long axis (Fig. 2) and there is no short intermolecular S. . . distance (<3.70 A; van der Waals distance), in spite of rather short interplanar distance (3.45 On the other hand, the BMDT-TTF molecules interrelated by the unit translation along the c axis are connected to each other by many short intermolecular S. . . S contacts (Fig. 3). Such a side-by-side arrangement is frequently observed in the crystals of molecular conductors based on the BEDT-TTF type donor or the dmit(dimercaptoisotrithione) complexes. 2) In addition to these intermolecular interaction parallel to the bc plane, we observe a intermolecular S(3) • • • S(3) distance (3.62 Å) between molecules interrelated by the translation vector a-b (and -a+b). All these structural features indicate that in this crystal there exist two-dimensional donor sheets which are parallel to the bc plane and weakly interrelated to each other along the a axis. multi-dimensional molecular arrangement, which is not based on the conventional column formation, is the most characteristic feature of the BMDT-TTF compounds.

In order to investigate the electronic structure, we first calculated the intermolecular overlap integrals (S) of HOMO of BMDT-TTF (Table 3).⁵⁾ The strongest interaction is observed along the side-by-side arrangement (S_C). The S_C value is larger than the corresponding S value in β -(BEDT-TTF)₂PF₆,⁶⁾ which is the first one-dimensional organic conductor along the side-by-side array. On the

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other hand, the $S_{\bf b}$ value (po-po type overlap) is rather small, as a result of the insufficient face-to-face overlapping (Fig. 2). The anisotropy $S_{\bf b}/S_{\bf c}{}^{\simeq}$ 0.4 is much larger than that in the Bechgaard salt (TMTSF)₂X (\simeq 0.1). The S_{-a+b} value indicates weak interaction among the donor sheets along the a axis.

The tight-binding approximation gives a simple two-dimensional energy band, $E(k)=2t_{b}cos(kb)+2t_{c}cos(kc),$

where we neglect the weak interactions, S_{-b+c} and S_{-a+b} . This energy band is half-filled and the Fermi surface contains largely distorted planes (Fig. 4).⁷⁾ This simple band picture predicts that this compound behaves as a metal. The resistivity measurement along the c axis, however, shows that this compound is a semiconductor (E_{a} = 0.12 eV) although the room-temperature conductivity (ca. 1 S cm⁻¹) is very high as a 1:1 salt (Fig. 5).

These results indicate that a simple band picture of non-interacting electrons does not suffice for the full understanding of the electronic structure. The introduction of on-site Coulomb repulsion would lead the system to the non-metallic state. This has been shown by preliminary ESR measurements. 8) (BMDT-TTF)SbF₆ exhibits a broad ESR signal (linewidth $\Delta B=21$ G) at room temperature when the static magnetic field is applied perpendicular to the c axis. The intensity decreases monotonously only by a factor of 0.5 from 300 K to 5 K, although the intensity for a semiconductor of a simple band model is expected to tend to vanish at low temperature.

In conclusion, (BMDT-TTF)SbF $_6$ is not a simple non-magnetic semiconductor. In any case, (BMDT-TTF)SbF $_6$ would be a prototype for the examination of the theory of the electron-electron interaction. Detailed ESR study will be reported elsewhere.

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(Received September 3, 1986)